



ThinKey™ Silicon Schottky Diode

Qualified per MIL-PRF-19500/723

Qualified Levels:
JAN, JANTX, and
JANTXV

DESCRIPTION

This Defense Logistics Agency (DLA) qualified Schottky diodes offer great value for aerospace and defense applications requiring high density power and excellent heat dissipation (typically 0.85 - 0.95 degrees C per Watt (C/W)). The 1N6910UTK2AS through 1N6912UTK2AS device polarity is anode-to-strap (standard) and is also available optionally in 1N6910UTK2CS through 1N6912UTK2CS as cathode-to-strap. This part can also be ordered in a strapless version. Up-screening for high-reliability applications is also available. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

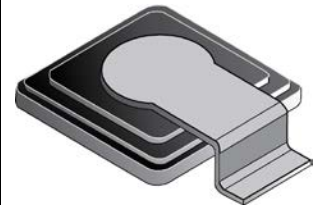
- JEDEC registered 1N6910 – 1N6912 number series.
- Oxide passivated structure.
- Guard ring protection for increased reverse energy capability.
- Epitaxial structure minimizes forward voltage drop.
- Hermetically sealed, low profile ceramic surface mount power package.
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/723. (See [part nomenclature](#) for all available options).
- RoHS compliant versions available (commercial grade only).

APPLICATIONS / BENEFITS

- Low package inductance.
- Very low thermal resistance.
- Also available with no strap as 1N6910UTK2, 1N6911UTK2 and 1N6912UTK2 by special request.
- Rugged ceramic and metal construction with no wire bonds.
- High surge capabilities and enable double-side cooling.

MAXIMUM RATINGS @ T_C = +25 °C, unless otherwise noted

| Parameters / Test Conditions | Symbol | Value | Unit |
|---|-------------------------------------|----------------|--------|
| Junction and Storage Temperature Range | T _j and T _{stg} | -65 to +150 | °C |
| Thermal Resistance Junction to Case (Anode-to-Strap) | R _{θJC} | 0.85 | °C/W |
| Thermal Resistance Junction to Case (Cathode-to-Strap) (Also applicable to strapless option) | R _{θJC} | 0.95 | °C/W |
| Working Peak Reverse Voltage: 1N6910UTK2,CS,AS 1N6911UTK2,CS,AS 1N6912UTK2,CS,AS | V _{RWM} | 15 30 45 | V |
| Average Rectified Output Current, T _C = +100 °C | I _O | 25 | A |
| Non-repetitive Peak Surge Current (t _p = 8.3 ms, half sine-wave) | I _{FSM} | 400 | A (pk) |



**ThinKey™ 2
Package**

MSC – Lawrence
6 Lake Street,
Lawrence, MA 01841
Tel: 1-800-446-1158 or
(978) 620-2600
Fax: (978) 689-0803

MSC – Ireland
Gort Road Business Park,
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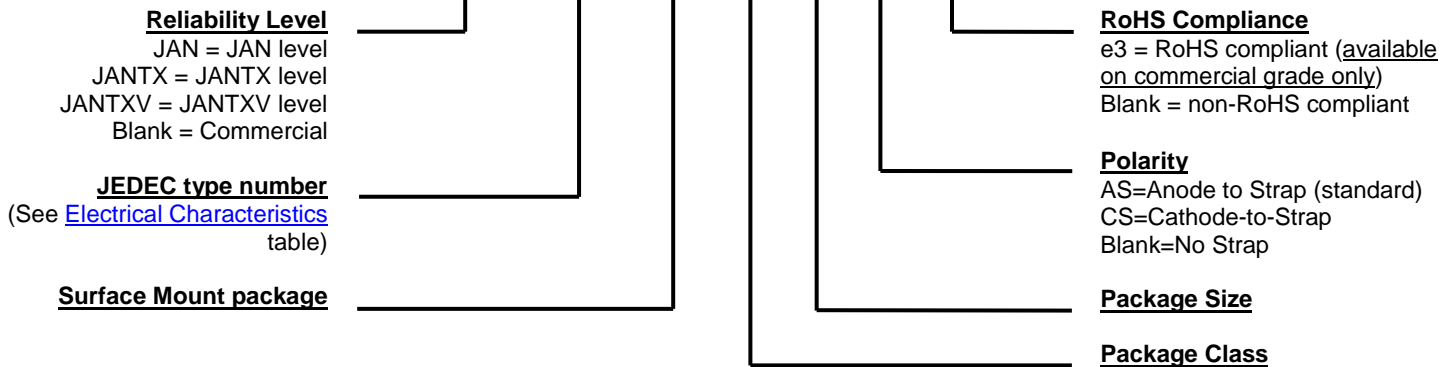
Website:
www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Ceramic-molybdenum Thinkey 2.
- TERMINALS: Tin/lead solder or RoHS compliant matte/tin (on commercial grade only) plating.
- MARKING: Part number and polarity symbol.
- POLARITY: Standard is anode to strap. Reverse is cathode to strap.
- WEIGHT: Approximately 0.5 grams.
- See [package dimensions](#) on page 4.

PART NOMENCLATURE

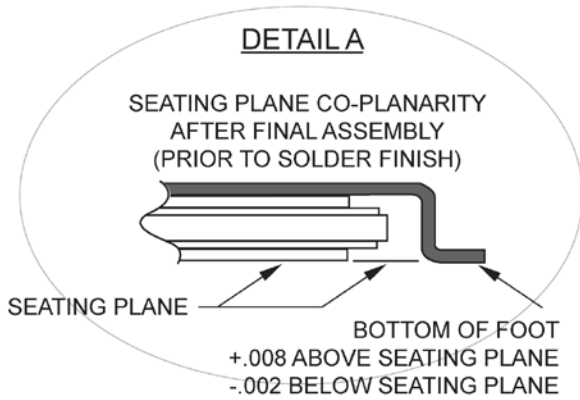
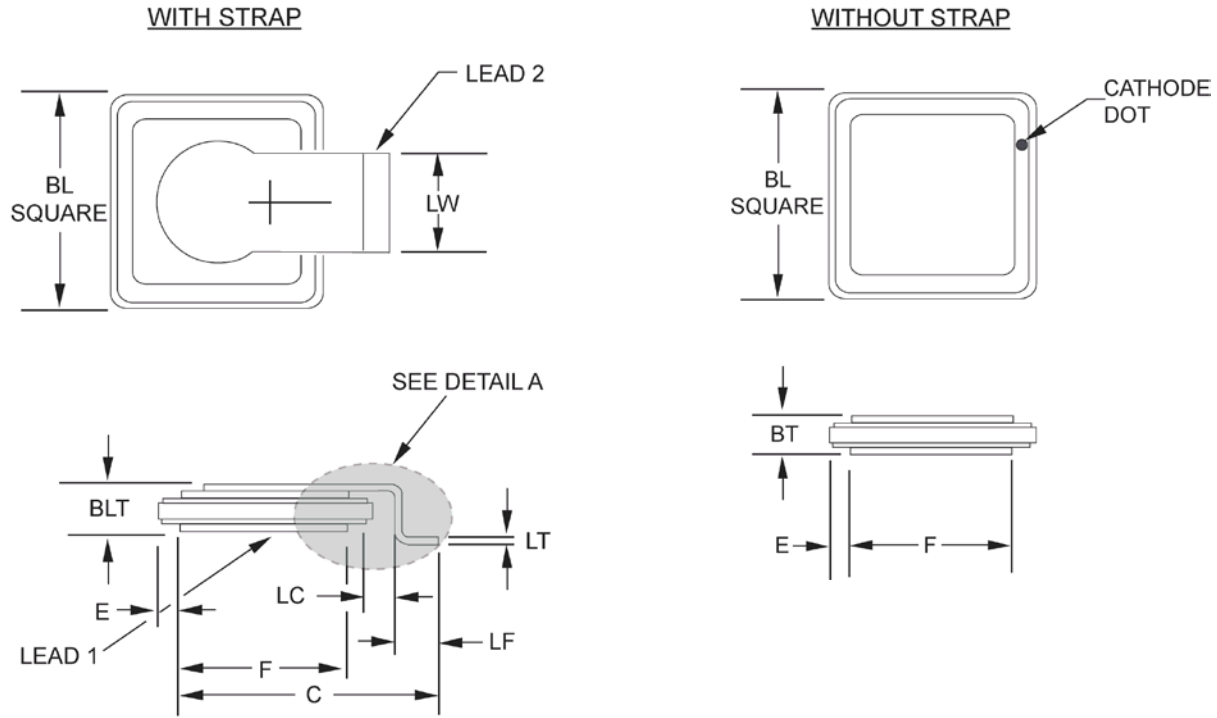
JAN 1N6910 U TK 2 AS (e3)


SYMBOLS & DEFINITIONS

| Symbol | Definition |
|----------------|---------------------|
| f | frequency |
| I _F | Forward current, dc |
| I _R | Reverse current, dc |
| T _C | Case temperature |
| t _p | Pulse time |
| V _R | Reverse Voltage, dc |

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^\circ\text{C}$, unless otherwise noted

| Parameters / Test Conditions | Symbol | MIN | MAX | Unit |
|---|--------------------|--------------------|------|------|
| Reverse (Leakage) Current $V_R = 15\text{ V}$, $T_C = 25\text{ }^\circ\text{C}$ $V_R = 30\text{ V}$, $T_C = 25\text{ }^\circ\text{C}$ $V_R = 45\text{ V}$, $T_C = 25\text{ }^\circ\text{C}$ | I _{R1} | 1N6910UTK2, CS, AS | 1.2 | mA |
| | | 1N6911UTK2, CS, AS | | |
| | | 1N6912UTK2, CS, AS | | |
| ----- $V_R = 15\text{ V}$, $T_C = +125\text{ }^\circ\text{C}$ $V_R = 30\text{ V}$, $T_C = +125\text{ }^\circ\text{C}$ $V_R = 45\text{ V}$, $T_C = +125\text{ }^\circ\text{C}$ | I _{R2} | 1N6910UTK2, CS, AS | 250 | mA |
| | | 1N6911UTK2, CS, AS | | |
| | | 1N6912UTK2, CS, AS | | |
| Forward Voltage Pulse test, pulse width $t_p = 300\text{ }\mu\text{s}$ $I_F = 10\text{ A (pk)}$, $T_C = +25\text{ }^\circ\text{C}$ | V _{F1} | 1N6910UTK2, CS, AS | 0.43 | V |
| | | 1N6911UTK2, CS, AS | 0.42 | |
| | | 1N6912UTK2, CS, AS | 0.52 | |
| ----- $I_F = 25\text{ A (pk)}$, $T_C = +25\text{ }^\circ\text{C}$ | V _{F2} | 1N6910UTK2, CS, AS | 0.52 | V |
| | | 1N6911UTK2, CS, AS | 0.54 | |
| | | 1N6912UTK2, CS, AS | 0.64 | |
| ----- $I_F = 25\text{ A (pk)}$, $T_C = +125\text{ }^\circ\text{C}$ | V _{F3} | 1N6910UTK2, CS, AS | 0.46 | V |
| | | 1N6911UTK2, CS, AS | 0.55 | |
| | | 1N6912UTK2, CS, AS | 0.63 | |
| Junction Capacitance $V_R = 5\text{ V}$, $f = 1\text{ MHz}$, $V_{SIG} = 50\text{ mV (p-p)}$ | C _J | 1N6910UTK2, CS, AS | 2000 | pF |
| | | 1N6911UTK2, CS, AS | 1250 | |
| | | 1N6912UTK2, CS, AS | 1000 | |
| Breakdown Voltage Pulse test, $t_p = 35\text{ ms}$ $I_R = 5.0\text{ mA (pk)}$, $T_C = 25\text{ }^\circ\text{C}$ | V _{(BR)1} | 1N6910UTK2, CS, AS | 16.5 | V |
| | | 1N6911UTK2, CS, AS | 33 | |
| | | 1N6912UTK2, CS, AS | 50 | |
| ----- $I_R = 5.0\text{ mA (pk)}$, $T_C = -55\text{ }^\circ\text{C}$ | V _{(BR)2} | 1N6910UTK2, CS, AS | 15 | V |
| | | 1N6911UTK2, CS, AS | 30 | |
| | | 1N6912UTK2, CS, AS | 45 | |

PACKAGE DIMENSIONS


| Ltr | Dimensions | | | |
|------------|------------|-------|-------------|-------|
| | Inch | | Millimeters | |
| | Min | Max | Min | Max |
| BL | 0.230 | 0.250 | 5.84 | 6.35 |
| BT | - | 0.125 | - | 3.18 |
| BLT | - | 0.115 | - | 2.92 |
| C | 0.293 | 0.333 | 7.44 | 8.46 |
| E | .023 NOM | | .58 NOM | |
| F | 0.171 | 0.181 | 4.34 | 4.60 |
| LC | .040 NOM | | 1.02 NOM | |
| LF | 0.055 | 0.075 | 1.40 | 1.91 |
| LT | 0.005 | 0.015 | 0.127 | 0.381 |
| LW | 0.085 | 0.115 | 2.16 | 2.92 |

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

SEE PAD LAYOUT ON NEXT PAGE.

PAD LAYOUT

